

| Ref # | Hits | Search Query | DBs | Default Operator | Plurals | Time Stamp |
|-------|------|---|--------------------|------------------|---------|------------------|
| S1 | 1347 | (438/14).CCLS. | USPAT; USOCR | OR | OFF | 2005/08/30 09:47 |
| S2 | 814 | S1 and (wafer with (semiconductor or conductor)) | US-PGPUB; USPAT | OR | ON | 2005/08/30 09:48 |
| S3 | 98 | S2 and "insulator" | US-PGPUB; USPAT | OR | ON | 2005/08/30 09:49 |
| S4 | 1 | S2 and "insulator" with region with "locally thin" | US-PGPUB; USPAT | OR | ON | 2005/08/30 09:50 |
| S5 | 1 | S2 and (region with "locally thin") | US-PGPUB; USPAT | OR | ON | 2005/08/30 09:50 |
| S6 | 1 | S1 and (insulator with "locally thin") | US-PGPUB; USPAT | OR | ON | 2005/08/30 09:51 |
| S7 | 6 | S1 and "locally thin" | US-PGPUB; USPAT | OR | ON | 2005/08/30 09:54 |
| S8 | 0 | "locally thin insulator" | US-PGPUB; USPAT | OR | ON | 2005/08/30 09:54 |
| S9 | 1420 | "thin insulator" | US-PGPUB; USPAT | OR | ON | 2005/08/30 09:54 |
| S10 | 229 | S9 and (wafer with (semiconductor or conductor)) | US-PGPUB; USPAT | OR | ON | 2005/08/30 10:04 |
| S11 | 810 | ((semiconductor or conductor) with insulator with "second conductor") | US-PGPUB; USPAT | OR | ON | 2005/08/30 10:05 |
| S12 | 2 | S11 with "locally thin" | US-PGPUB; USPAT | OR | ON | 2005/08/30 10:06 |
| S13 | 2 | S11 and "locally thin" | US-PGPUB; USPAT | OR | ON | 2005/08/30 10:07 |
| S14 | 2 | S11 and ("locally thin" with (silicon oxide film or SiO2)) | US-PGPUB; USPAT | OR | ON | 2005/08/30 10:08 |
| S15 | 292 | S11 and (thin with (silicon oxide film or SiO2)) | US-PGPUB; USPAT | OR | ON | 2005/08/30 10:08 |
| S16 | 525 | S11 and (thin region with (silicon oxide film or SiO2)) | US-PGPUB; USPAT | OR | ON | 2005/08/30 10:11 |
| S17 | 2 | S11 and ("thin region" with (silicon oxide film or SiO2)) | US-PGPUB; USPAT | OR | ON | 2005/08/30 10:11 |
| S18 | 4 | S11 and ("thin region") | US-PGPUB; USPAT | OR | ON | 2005/08/30 11:12 |
| S19 | 1 | ("4697330").PN. | USPAT; USOCR | OR | OFF | 2005/08/30 11:53 |
| S20 | 0 | "plasma etching" with "solid angle" | US-PGPUB; USPAT | OR | ON | 2005/08/30 11:54 |
| S21 | 103 | (plasma with "solid angle") | US-PGPUB; USPAT | OR | ON | 2005/12/15 12:17 |
| S22 | 6972 | "solid angle" | US-PGPUB; USPAT | OR | ON | 2005/08/30 13:47 |

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| S23 | 0 | S22 and (conductor with "insulator on second conductor") | US-PGPUB; USPAT | OR | ON | 2005/08/30 13:48 |
| S24 | 0 | S22 and (conductor with "insulator on conductor") | US-PGPUB; USPAT | OR | ON | 2005/08/30 13:48 |
| S25 | 82 | S22 and (conductor with insulator) | US-PGPUB; USPAT | OR | ON | 2005/08/30 14:04 |
| S26 | 2 | S25 and ("this region" or "locally thin") | US-PGPUB; USPAT | OR | ON | 2005/08/30 13:50 |
| S27 | 0 | S25 and ("this region") | US-PGPUB; USPAT | OR | ON | 2005/08/30 13:50 |
| S28 | 3 | S25 and ("thin region") | US-PGPUB; USPAT | OR | ON | 2005/08/30 13:50 |
| S29 | 3 | S25 and ("thin region" or "locally thin") | US-PGPUB; USPAT | OR | ON | 2005/08/30 13:50 |
| S30 | 19 | S22 and "thin region" | US-PGPUB; USPAT | OR | ON | 2005/08/30 14:06 |
| S31 | 0 | S22 and "silicon nitride film" with "thin region" | US-PGPUB; USPAT | OR | ON | 2005/08/30 14:13 |
| S32 | 8 | S22 and thin with "silicon nitride film" | US-PGPUB; USPAT | OR | ON | 2005/08/30 14:24 |
| S33 | 19 | S22 and thin adj1 region | US-PGPUB; USPAT | OR | ON | 2005/08/30 14:25 |
| S34 | 49 | measuring same "ion current density" | US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB | OR | OFF | 2005/12/13 12:29 |
| S37 | 25 | "first region" with (ion and electron) with "second region" | US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB | OR | OFF | 2005/12/13 12:35 |
| S38 | 7 | (ion and electron) with launched | US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB | OR | OFF | 2005/12/13 12:36 |
| S39 | 281423 | wafer | US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB | OR | OFF | 2005/12/13 12:36 |
| S40 | 7181 | S39 and ((first or second) adj region) | US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB | OR | OFF | 2005/12/13 12:37 |

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| S41 | 4780 | S40 and (ion or electron) | US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB | OR | OFF | 2005/12/13 12:37 |
| S42 | 1782 | S41 and plasma | US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB | OR | OFF | 2005/12/13 12:37 |
| S43 | 2 | S42 and (measuring with "ion current density") | US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB | OR | OFF | 2005/12/13 12:38 |
| S44 | 10 | S42 and "ion current density" | US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB | OR | OFF | 2005/12/13 12:38 |
| S45 | 1041 | "ion current density" | US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB | OR | OFF | 2005/12/13 14:13 |
| S46 | 17 | S45 and "measuring method" | US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB | OR | OFF | 2005/12/13 14:16 |
| S47 | 71 | S45 and (measuring with method) | US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB | OR | OFF | 2005/12/13 14:16 |
| S48 | 26 | S47 and electrons | US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB | OR | OFF | 2005/12/13 14:16 |
| S49 | 4 | ("5840199" "5850042" "5969393" "6127255").PN. | US-PGPUB; USPAT; USOCR | OR | OFF | 2005/12/13 14:22 |
| S50 | 24994 | wafer same plasma | US-PGPUB; USPAT; USOCR | OR | OFF | 2005/12/14 13:29 |
| S51 | 1604 | S50 and (ion same electrons) | US-PGPUB; USPAT; USOCR | OR | OFF | 2005/12/13 15:31 |

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| S52 | 107 | S51 and "ion current density" | US-PGPUB; USPAT; USOCR | OR | OFF | 2005/12/13 14:23 |
| S53 | 18 | S52 and measure | US-PGPUB; USPAT; USOCR | OR | OFF | 2005/12/13 14:23 |
| S54 | 24332 | (ion same electrons) | US-PGPUB; USPAT; USOCR | OR | OFF | 2005/12/13 15:32 |
| S55 | 1198 | S54 and "plasma etching" | US-PGPUB; USPAT; USOCR | OR | OFF | 2005/12/13 15:32 |
| S56 | 83 | S55 and "ion current density" | US-PGPUB; USPAT; USOCR | OR | OFF | 2005/12/13 15:32 |
| S57 | 4 | ("2002/0123229").URPN. | USPAT | OR | OFF | 2005/12/14 11:42 |
| S58 | 1041 | "ion current density" | US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB | OR | OFF | 2005/12/14 12:38 |
| S59 | 71 | S58 and (measuring with method) | US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB | OR | OFF | 2005/12/14 12:40 |
| S60 | 4 | S59 and criterion | US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB | OR | OFF | 2005/12/14 12:41 |
| S61 | 220 | S58 and wafer same plasma | US-PGPUB; USPAT; USOCR | OR | OFF | 2005/12/14 13:47 |
| S62 | 4 | S61 and criterion | US-PGPUB; USPAT; USOCR | OR | OFF | 2005/12/14 13:29 |
| S63 | 138 | S61 and (ion same electron) | US-PGPUB; USPAT; USOCR | OR | OFF | 2005/12/15 12:39 |
| S64 | 5 | ((("4585516") or ("5298112") or ("5625526") or ("5593539") or ("5779925"))).PN. | US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB | OR | OFF | 2005/12/14 14:03 |
| S65 | 3 | "measured ion current density" | US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB | OR | OFF | 2005/12/14 14:46 |

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| S66 | 142 | (measured same "ion current density") | US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB | OR | OFF | 2005/12/14 14:47 |
| S67 | 8 | S66 and (manufacturing same based) | US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB | OR | OFF | 2005/12/14 14:47 |
| S68 | 1 | "device based" same "ion current density" | US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB | OR | OFF | 2005/12/14 15:04 |
| S69 | 51 | " based" same "ion current density" | US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB | OR | OFF | 2005/12/14 15:06 |
| S70 | 0 | " manufactured based" same "ion current density" | US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB | OR | OFF | 2005/12/14 15:06 |
| S71 | 0 | " manufactured based" with "ion current density" | US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB | OR | OFF | 2005/12/14 15:07 |
| S72 | 0 | S58 and "manufactured based" | US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB | OR | OFF | 2005/12/14 15:07 |
| S73 | 26 | ("5102687" "5474648").PN. OR ("5779925").URPN. | US-PGPUB; USPAT; USOCR | OR | OFF | 2005/12/15 12:00 |
| S74 | 31 | (conductor with "solid angle") | US-PGPUB; USPAT | OR | ON | 2005/12/15 12:21 |
| S75 | 7234 | ("solid angle") | US-PGPUB; USPAT | OR | ON | 2005/12/15 12:22 |
| S76 | 1067 | S75 and ((2nd or second) with region) | US-PGPUB; USPAT | OR | ON | 2005/12/15 12:35 |
| S77 | 831 | S76 and ((1st or first) with region) | US-PGPUB; USPAT | OR | ON | 2005/12/15 12:36 |
| S78 | 148 | S77 and conductor | US-PGPUB; USPAT | OR | ON | 2005/12/15 12:24 |
| S79 | 124 | S75 and ("2nd region" or "second region") | US-PGPUB; USPAT | OR | ON | 2005/12/15 12:36 |

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| S80 | 103 | S79 and ("1st region" or "first region") | US-PGPUB; USPAT | OR | ON | 2005/12/15 12:36 |
| S81 | 1041 | "ion current density" | US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB | OR | OFF | 2005/12/15 12:39 |
| S82 | 220 | S81 and wafer same plasma | US-PGPUB; USPAT; USOCR | OR | OFF | 2005/12/15 12:39 |
| S83 | 138 | S82 and (ion same electron) | US-PGPUB; USPAT; USOCR | OR | OFF | 2005/12/15 12:39 |
| S84 | 2 | S83 and "solid angle" | US-PGPUB; USPAT; USOCR | OR | OFF | 2005/12/15 12:39 |